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### FDG328P

### P-Channel 2.5V Specified PowerTrench® MOSFET

### **General Description**

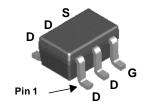
This P-Channel 2.5V specified MOSFET is produced in a rugged gate version of Fairchild Semiconductor's advanced PowerTrench process. It has been optimized for power management applications for a wide range of gate drive voltages (2.5V – 12V).

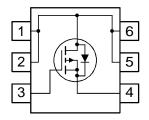
### **Applications**

- Load switch
- Power management
- DC/DC converter

### **Features**

- -1.5 A, -20 V.  $R_{DS(ON)} = 0.145 \Omega$  @  $V_{GS} = -4.5 V$  $R_{DS(ON)} = 0.210 \Omega$  @  $V_{GS} = -2.5 V$
- Low gate charge
- High performance trench technology for extremely low Roscom
- Compact industry standard SC70-6 surface mount package





### SC70-6

### Absolute Maximum Ratings T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V <sub>DSS</sub>	Drain-Source Voltage		-20	V
V <sub>GSS</sub>	Gate-Source Voltage		± 12	V
I <sub>D</sub>	Drain Current - Continuous	(Note 1a)	-1.5	А
	- Pulsed		-6	
P <sub>D</sub>	Power Dissipation for Single Operation	(Note 1a)	0.75	W
		(Note 1b)	0.48	
$T_J$ , $T_{STG}$	Operating and Storage Junction Temperature Range		-55 to +150	°C

### **Thermal Characteristics**

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1b)	260	°C/W
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**Package Marking and Ordering Information** 

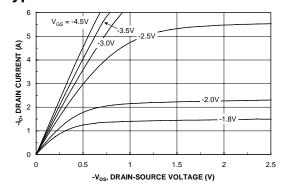
Device Marking	Device	Reel Size	Tape width	Quantity
.28	FDG328P	7"	8mm	3000 units

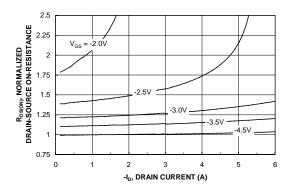
Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Cha	racteristics		I	I	I	
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	-20			V
ΔBV <sub>DSS</sub> ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	$I_D$ = -250 $\mu$ A, Referenced to 25°C		<b>-</b> 9		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = -16 \text{ V},  V_{GS} = 0 \text{ V}$			-1	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage, Forward	$V_{GS} = 12 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage, Reverse	$V_{GS} = -12 \text{ V},  V_{DS} = 0 \text{ V}$			-100	nA
On Chai	racteristics (Note 2)					
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-0.6		-1.5	>
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250 \mu\text{A}$ , Referenced to 25°C	$_{D}$ = -250 $\mu$ A, Referenced to 25°C 3			mV/°C
$R_{\text{DS(on)}}$	Static Drain–Source On–Resistance	$V_{GS} = -4.5 \text{ V},  I_D = -1.5 \text{ A}$ $V_{GS} = -2.5 \text{ V},  I_D = -1.2 \text{ A}$ $V_{GS} = -4.5 \text{ V}, I_D = -1.5 \text{ A}, T_J = 125 ^{\circ}\text{C}$	120 169 156		145 210 203	mΩ
I <sub>D(on)</sub>	On-State Drain Current	$V_{GS} = -4.5 \text{ V}, I_D = -1.5 \text{ A}, T_J=125^{\circ}\text{C}$ $V_{GS} = -4.5 \text{ V}, V_{DS} = -5 \text{ V}$	-3			Α
<b>g</b> FS	Forward Transconductance	$V_{DS} = -5 \text{ V}, \qquad I_{D} = -1.5 \text{ A}$		5		S
Dynami	c Characteristics					
C <sub>iss</sub>	Input Capacitance	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V},$		337	7	pF
Coss	Output Capacitance	f = 1.0 MHz		88		pF
C <sub>rss</sub>	Reverse Transfer Capacitance		51			pF
Switchin	ng Characteristics (Note 2)					
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = -10 \text{ V}, I_D = 1 \text{ A},$		9	18	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{GS} = -4.5 \text{ V}, R_{GEN} = 6 \Omega$		12	22	ns
$t_{d(off)}$	Turn-Off Delay Time		10		20	ns
t <sub>f</sub>	Turn-Off Fall Time			5	10	ns
$Q_g$	Total Gate Charge	$V_{DS} = -10 \text{ V}, I_{D} = -1.5 \text{ A},$		3.7	6	nC
$Q_{gs}$	Gate-Source Charge	$V_{GS} = -4.5 \text{ V}$		0.7	,	nC
$Q_{gd}$	Gate-Drain Charge			1.3	3	nC
Drain-S	ource Diode Characteristics	and Maximum Ratings				
Is	Maximum Continuous Drain-Sourc	<u> </u>		-0.62	Α	
V <sub>SD</sub>	Drain–Source Diode Forward Voltage	$V_{GS} = 0 \text{ V},  I_{S} = -0.62 \text{ A (Note 2)}$		-0.7	-1.2	V

#### Notes:

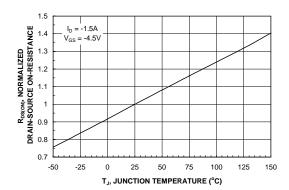
- 1. R<sub>0JA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>0JC</sub> is guaranteed by design while R<sub>0CA</sub> is determined by the user's board design.
  - a.) 170°/W when mounted on a 1 in² pad of 2 oz. copper.
  - b.) 260°/W when mounted on a minimum pad.
- 2. Pulse Test: Pulse Width < 300µs, Duty Cycle < 2.0%

### **Typical Characteristics**





#### Characteristics



Current

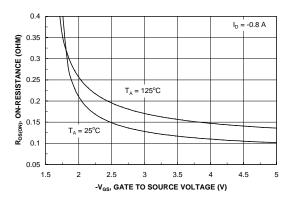


Figure 3. On-Resistance Variation withTemperature.

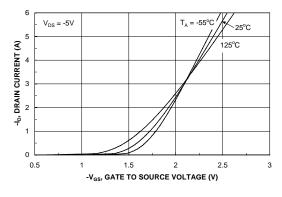


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

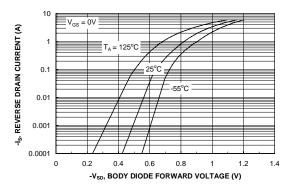
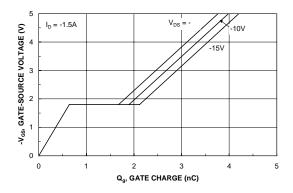


Figure 5. Transfer Characteristics.

Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

### **Typical Characteristics**



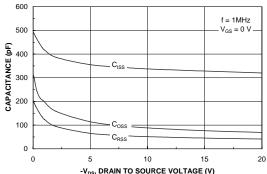


Figure 7. Gate Charge Characteristics.

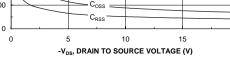
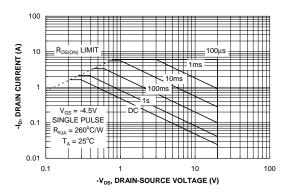


Figure 8. Capacitance Characteristics.



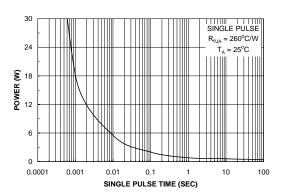


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

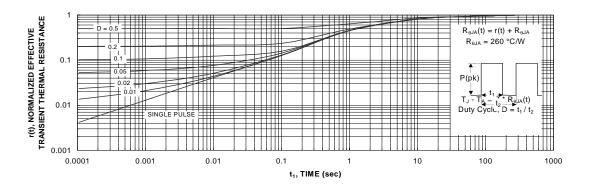


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c.
Transient themal response will change depending on the circuit board design.

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